



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Jae-Hak KIM, et al.

Confirmation No. 2739

Serial No. 09/919,340

Examiner: Erdem, Fazli

Filed: July 30, 2001

Group Art Unit: 2826

For: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE CAPABLE OF
REDUCING PARASITIC CAPACITANCE AND SEMICONDUCTOR DEVICE
THEREBY

BOX NON FEE AMENDMENT
Assistant Commissioner for Patents,
Washington, D.C. 20231

Responsive to the Office Action dated December 20, 2002, enclosed is an amendment in the
above-identified application.

The fee has been calculated as shown below.

CLAIMS AS AMENDED					
For:	Number After Amendment	Previous Number	Extra	Rate	Additional Fee
Total Claims	15	15	0	x \$18 =	\$0.00
Independent Claims	3	3	0	x \$84 =	\$0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00

*greater of twenty (20) or number for which fee has been paid
**greater of three (3) or number for which fee has been paid

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☐ Any deficiency or overpayment should be charged or credited to deposit account number 13-1703.

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.



20575

PATENT TRADEMARK OFFICE

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1030 SW Morrison Street

2001-2002-2003

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3-20-03
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#8/B

PATENT APPLICATION
Doc. No. 4591-183

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

4/2/03

In re application of: Jae-Hak KIM, et al.

Confirmation No. 2739

Serial No. 09/919,340

Examiner: Erdem, Fazli

John H

Filed: July 30, 2001

Group Art Unit: 2826

For: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE CAPABLE
OF REDUCING PARASITIC CAPACITANCE AND SEMICONDUCTOR
DEVICE THEREBY

BOX NON-FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

RESPONSE TO OFFICE ACTION

Responsive to the Office Action, dated December 20, 2002, please amend the
application as follows.

IN THE CLAIMS

1. (Twice amended) A method for fabricating a semiconductor device, comprising:
forming a conductive region on a substrate;
depositing a lower inorganic silicon oxide layer on the substrate;
sequentially depositing an organic silicon oxide layer of a low dielectric constant on
the lower inorganic silicon oxide layer;
forming a partial trench with a predetermined depth in the organic silicon oxide layer;
oxygenating an inner wall of the partial trench such that the organic silicon oxide
layer organic silicon oxide layer changes to an upper inorganic silicon oxide; and
forming a trench by etching the partial trench.
2. (Once amended) The method of claim 1 comprising:
depositing a conductive layer to fill the trench; and
removing a portion of the conductive layer stacked on a top surface of the organic